

## **Publications from the Technology Platform "Power Electronics" of the Research Fab Microelectronics Germany (2022)**

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- Tsao Y.-F., Hsu H.-S., Wurfl J., Hsu H.-T. (2022): Dual-Band Power Amplifier Design at 28/38 GHz for 5G New Radio Applications. In: IEEE Access, Vol. 10, pp. 77826-77836 (Article). DOI:10.1109/ACCESS.2022.3193695. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85135578442&doi=10.1109%2fACCESS.2022.3193695&partnerID=40&md5=f8c89d67e775dc9c647b56fb5b5c34a3>
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- Bucher T., Grzyb J., Hillger P., Rucker H., Heinemann B., Pfeiffer U.R. (2022): A Broadband 300 GHz Power Amplifier in a 130 nm SiGe BiCMOS Technology for Communication Applications. In: IEEE Journal of Solid-State Circuits, Vol.57, Nr.7, pp.2024-2034 (Article). DOI:10.1109/JSSC.2022.3162079. Link: <https://www.scopus.com/inward/record.uri?eid=2-s2.0-85128261001&doi=10.1109%2fJSSC.2022.3162079&partnerID=40&md5=457d816518e3ab34e5e020869a1b63f2>
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